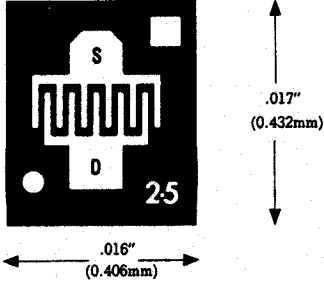


CHIP NUMBER  
**FN3.6**



Die Size: .16 x .17 (mils)  
 0.406 x 0.432(mm)  
 3 x 3 (mils)  
 Pad Size: 0.076 x 0.076(mm)  
 GATE-SUBSTRATE

**CONTACT METALLIZATION**

Top Contact: > 12,000  
 Å Aluminum

Backside Contact: 3,000 Å Gold

**ASSEMBLY RECOMMENDATIONS**

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

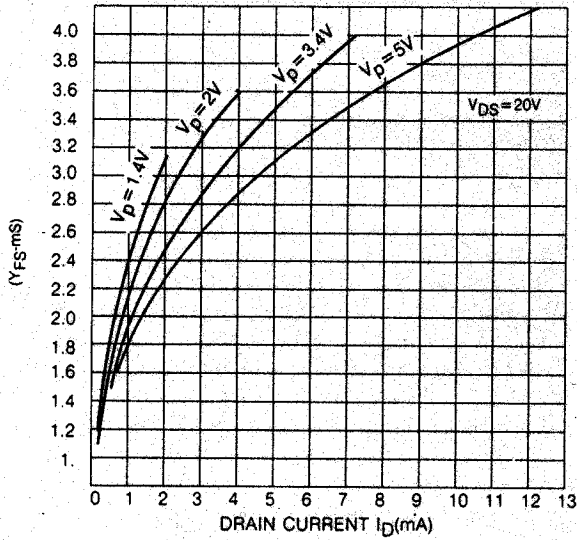
**TYPICAL ELECTRICAL CHARACTERISTICS**

| PARAMETER            | MIN. | TYP  | MAX. | UNIT | TEST CONDITIONS                                      |
|----------------------|------|------|------|------|--|
| B <sub>VGS</sub>     | -30  | -50  | -70  | V    | V <sub>DS</sub> = 0, I <sub>G</sub> = 1μA            |
| I <sub>DSS</sub>     | 0.5  | 8.0  | 20   | mA   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0           |
| g <sub>fs</sub>      | 1.5  | 4.0  | 6.0  | mmho | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0           |
| I <sub>GSS</sub>     |      | 25   | 100  | pA   | V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0          |
| r <sub>DS</sub>      | 150  | 200  | 600  | Ω    | V <sub>DS</sub> = 100mV, V <sub>GS</sub> = 0         |
| V <sub>GS(off)</sub> | -1.0 | -3.0 | 8.0  | V    | V <sub>DS</sub> = 15V, I <sub>D</sub> = 1nA          |
| C <sub>rss</sub>     | 1.2  | 2.0  | 3.0  | pF   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0, f = 1MHz |
| C <sub>iss</sub>     |      | 4.5  | 6.0  | pF   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0, f = 1MHz |

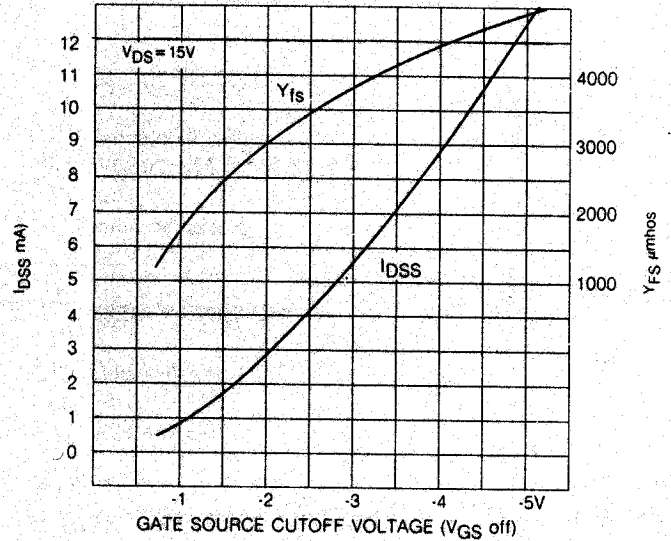
TYPICAL DEVICE TYPES: 2N3821 - 2N3824, 2N3921 - 2N3922, 2N5545 - 2N5547

**CHIP TYPE FN3.6**

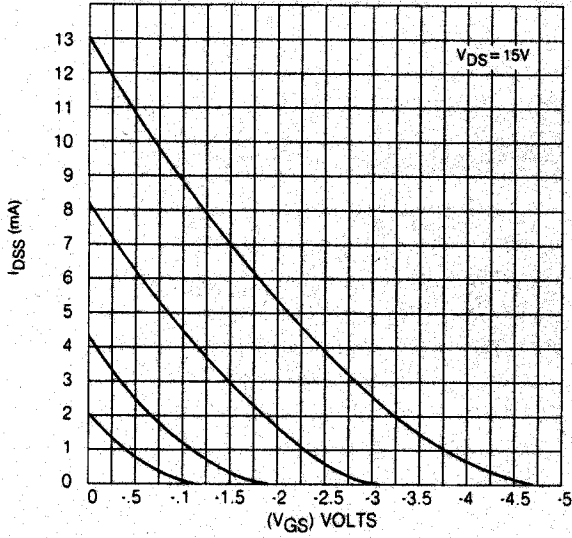
**FORWARD TRANSADMITTANCE VS. OPERATING DRAIN CURRENT**



**FORWARD TRANSADMITTANCE VS.**



**TRANSFER CHARACTERISTICS**



**OUTPUT CHARACTERISTICS**

